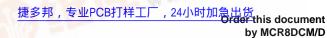
# SEMICONDUCTOR TECHNICAL DATA



by MCR8DCM/D

MCR8DCM

MCR8DCN

Motorola Preferred Devices

# **Silicon Controlled Rectifiers Reverse Blocking Thyristors**

Designed for high volume, low cost, industrial and consumer applications such as motor control; process control; temperature, light and speed control.

DZSC.COM

- Small Size
- · Passivated Die for Reliability and Uniformity
- Low Level Triggering and Holding Characteristics
- Available in Two Package Styles Surface Mount Lead Form — Case 369A Miniature Plastic Package — Straight Leads — Case 369

#### **ORDERING INFORMATION**

- To Obtain "DPAK" in Surface Mount Leadform (Case 369A) Shipped in Sleeves - No Suffix, i.e. MCR8DCN Shipped in 16 mm Tape and Reel - Add "T4" Suffix to Device Number, i.e. MCR8DCNT4
- To Obtain "DPAK" in Straight Lead Version (Case 369) Shipped in Sleeves Add "-1" Suffix to Device Number, i.e. MCR8DCN-1

#### **MAXIMUM RATINGS** (T<sub>1</sub> = 25°C unless otherwise noted)

Rating		Symbol	Value	Unit
Peak Repetitive Off-State Voltage (1) Peak Repetitive Reverse Voltage (TJ = -40 to 125°C)	MCR8DCM MCR8DCN	V <sub>DRM</sub> V <sub>RRM</sub>	600 800	Volts
On–State RMS Current (All Conduction Angles; T <sub>C</sub> = 105°C)		<sup>I</sup> T(RMS)	8.0	Amps
Average On–State Current (All Conduction Angles; $T_C = 105^{\circ}C$ )	1900	I <sub>T(AV)</sub>	5.1	
Peak Non–Repetitive Surge Current (One Half Cycle, 60 Hz, TJ = 125°C)	100	ITSM	80	
Circuit Fusing Consideration (t = 8.3 msec)		l <sup>2</sup> t	26	A <sup>2</sup> sec
Peak Gate Power (Pulse Width ≤ 10 μsec, T <sub>C</sub> = 105°C)		PGM	5.0	Watts
Average Gate Power (t = 8.3 msec, $T_C$ = 105°C)		P <sub>G(AV)</sub>	0.5	a,
Peak Gate Current (Pulse Width $\leq$ 10 µsec, T <sub>C</sub> = 105°C)		IGM	2.0	Amps
Operating Junction Temperature Range		TJ	-40 to 125	°C
Storage Temperature Range	890 1	T <sub>stg</sub>	-40 to 150	

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance — Junction to Case — Junction to Ambient — Junction to Ambient (2)	R <sub>θ</sub> JC R <sub>θ</sub> JA R <sub>θ</sub> JA	2.2 88 80	°C/W
Maximum Lead Temperature for Soldering Purposes (3)	Т	260	°C

(1) VDRM for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the device are exceeded.

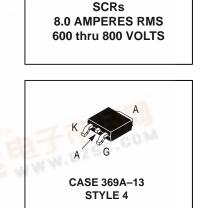
(2) Surface mounted on minimum recommended pad size.

(3) 1/8" from case for 10 seconds.

referred devices are Motorola recommended choices for future use and best overall value.

df.dzsc.com





**ELECTRICAL CHARACTERISTICS** (T<sub>J</sub> =  $25^{\circ}$ C unless otherwise noted)

Characteristics	Symbol	Min	Тур	Max	Unit
Peak Forward Blocking CurrentPeak Reverse Blocking Current $(V_{AK} = Rated V_{DRM} \text{ or } V_{RRM}, Gate Open)$ TJ = 25°CTJ = 25°C	I <sub>DRM</sub> I <sub>RRM</sub>		_	0.01	mA
$T_{J} = 125^{\circ}C$ Peak On–State Voltage (1) (I <sub>TM</sub> = 16 A)	VTM		1.4	5.0 1.8	Volts
Gate Trigger Current (Continuous dc) $(V_D = 12 \text{ V}, \text{ R}_L = 100 \Omega, \text{ T}_J = 25^{\circ}\text{C})$ $(V_D = 12 \text{ V}, \text{ R}_L = 100 \Omega, \text{ T}_J = -40^{\circ}\text{C})$	IGT	2.0	7.0 —	15 30	mA
Gate Trigger Voltage (Continuous dc) $(V_D = 12 \text{ V}, \text{ R}_L = 100 \Omega, \text{ T}_J = 25^{\circ}\text{C})$ $(V_D = 12 \text{ V}, \text{ R}_L = 100 \Omega, \text{ T}_J = -40^{\circ}\text{C})$ $(V_D = 12 \text{ V}, \text{ R}_L = 100 \Omega, \text{ T}_J = 125^{\circ}\text{C})$	VGT	0.5 — 0.2	0.65 — —	1.0 2.0 —	Volts
Holding Current $(V_D = 12 \text{ V}, \text{ I}_T = 200 \text{ mA}, \text{ T}_J = 25^{\circ}\text{C})$ $(V_D = 12 \text{ V}, \text{ I}_T = 200 \text{ mA}, \text{ T}_J = -40^{\circ}\text{C})$	ΙΗ	4.0	22 —	30 60	mA
Latching Current ( $V_D = 12 V$ , $I_G = 15 mA$ , $T_J = 25^{\circ}C$ ) ( $V_D = 12 V$ , $I_G = 30 mA$ , $T_J = -40^{\circ}C$ )	ΙL	4.0	22 —	30 60	mA

## DYNAMIC CHARACTERISTICS

Characteristics	Symbol	Min	Тур	Max	Unit
Critical Rate of Rise of Off-State Voltage	dv/dt				V/μs
(V <sub>D</sub> = Rated V <sub>DRM</sub> , Exponential Waveform, Gate Open, $T_J$ = 125°C)		50	200	—	

(1) Pulse Test; Pulse Width  $\leq$  2.0 msec, Duty Cycle  $\leq$  2%.

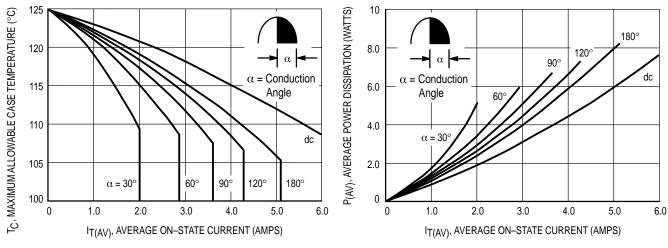


Figure 1. Average Current Derating



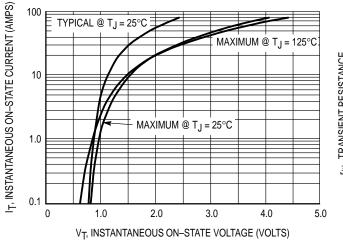


Figure 3. On–State Characteristics

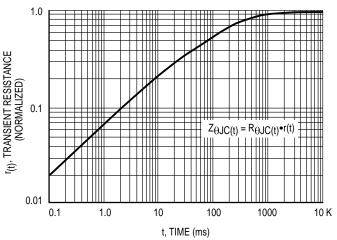
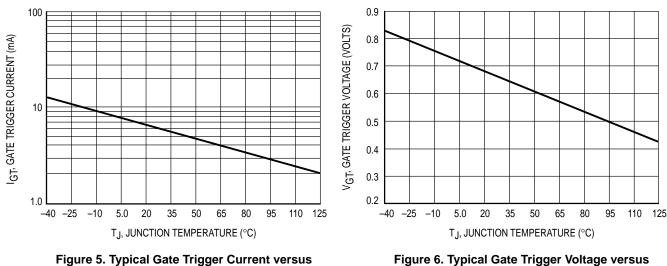


Figure 4. Transient Thermal Response







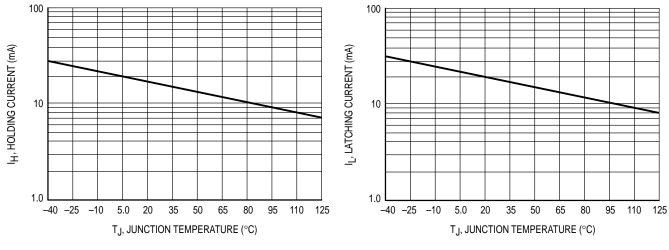
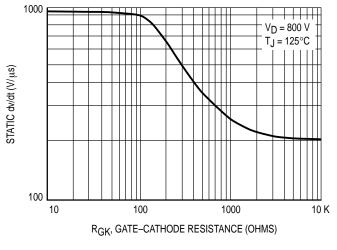
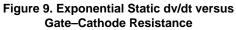
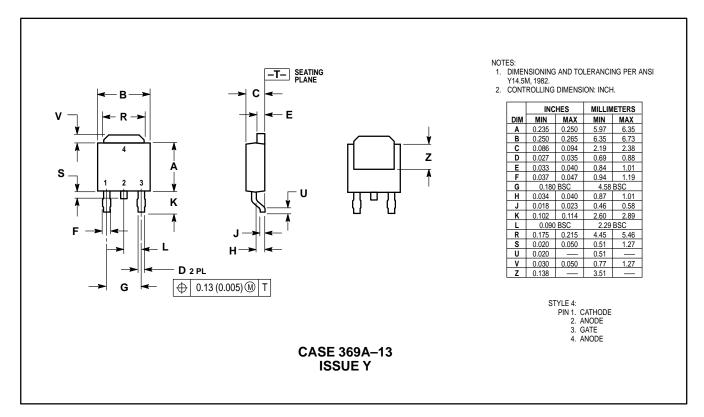




Figure 8. Typical Latching Current versus Junction Temperature







# PACKAGE DIMENSIONS

Motorola reserves the right to make changes without further notice to any products herein. Motorola makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does Motorola assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation consequential or incidental damages. "Typical" parameters which may be provided in Motorola data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. Motorola does not convey any license under its patent rights nor the rights of others. Motorola products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the Motorola product could create a situation where personal injury or death may occur. Should Buyer purchase or use Motorola products for any such unintended or unauthorized application, Buyer shall indemnify and hold Motorola and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that Motorola was negligent regarding the design or manufacture of the part. Motorola and (A) are registered trademarks of Motorola, Inc. Motorola, Inc. is an Equal Opportunity/Affirmative Action Employer.

#### How to reach us:

USA/EUROPE/Locations Not Listed: Motorola Literature Distribution;

Mfax is a trademark of Motorola, Inc. JAPAN: Nippon Motorola Ltd.: SPD, Strategic Planning Office, 4-32-1,

P.O. Box 5405, Denver, Colorado 80217. 303-675-2140 or 1-800-441-2447

Mfax™: RMFAX0@email.sps.mot.com - TOUCHTONE 602-244-6609

INTERNET: http://motorola.com/sps

- US & Canada ONLY 1-800-774-1848



ASIA/PACIFIC: Motorola Semiconductors H.K. Ltd.; 8B Tai Ping Industrial Park, 51 Ting Kok Road, Tai Po, N.T., Hong Kong. 852-26629298

Nishi-Gotanda, Shinagawa-ku, Tokyo 141, Japan. 81-3-5487-8488